Development of HVCMOS-based 中国物理学会高能物理分会 silicon tracker for CEPC HIGH ENERGY PHYSICS BRANCH OF CPS Xiaojie Jiang (姜啸捷) Institute of High Energy Physics, Contact: on behalf of CEPC Silicon Tracker Team jiangxj@ihep.ac.cn Chinese Academy of Sciences 1.Abstract The CEPC physics programs unanimously rely on a high-resolution, fine-pitch, low-material and fast-readout tracking system with a large-area coverage. CEPC has an average bunch spacing of 0.68µs for the Higgs factory operation and 25ns for the Z factory operation with a high luminosity (peak luminosity for $Z \sim 10^{36} \text{cm}^{-2}\text{s}^{-1}$). In order to overcome these challenges, It's necessary to use large area monolithic pixel sensor silicon. This technology has been developing fast. The High Voltage Metal-Oxide-Semiconductor (HVCMOS) technology is a promising candidate. Latest development based on ATLASPix3 sensor prototypes will be reported, including efforts to characterising the sensor performance in beamtest using electron beam at DESY. 2.Introduction 3.Test Modules □ Si Tracker for CEPC **□** Single chip module "GECCO MAB v2







- Tuning and readout for single chip
- Generic Configuration and COntrol
 - System designed at KIT, produced
- in China
- ► LFP-FMC connection to Nexys FPGA,

CEPC requires a high-resolution and low-material tracking system especially for momentum measurement

 $(\sigma_{1/pt} = 2 \times 10^{-5} \oplus \frac{1 \times 10^{-3}}{p \sin^{3/2} \theta} \text{ GeV}^{-1})$. The three figures above are potential designs for CEPC. Without doubt, CEPC tracker will use large area silicon. Over $70m^2$ for silicon + TPC/DC designs, about $140m^2$ for full silicon design. HVCMOS is an economical and effective candidate.

■ **C** Sensor technology

R&D is carried so far with ATLASPix3, a High-Voltage CMOS pixel sensor designed by KIT

- ➢ 180nm HVCMOS technology of TSI
- \blacktriangleright Pixel size 50 × 150 µm²(or smaller)
- \succ 132 columns \times 372 rows (20.2 \times 21 mm² chip size)
- ➤ Material budget for tracker layers: ~0.65% (TPC/Si)/, ~1% (Full Si) X0 / layer
- \blacktriangleright Binary with ToT(Time over Threshold) information(time bin size 25ns)
- Triggerless(1.6 Gbps with 8b/10b coding) /triggered(1.28 Gbps with 64b/66b coding) readout possible





Block scheme of the pixel matrix and column circuits

- PCIe x16 to DUT, allows extensive tests
- Carrier board for ATLASPix3 single-chip,
- produced in China

Quad module



Four chips sharing services by common power connections and configuration lines for large area application

NexvsVideo **FPGA** board

- > Data flex and power cables designed by INFN Milano, under verification
- Adapter card for connecting to GECCO

Telescope module

- Readout up to four chips. When use triggerless mode : each sensor provides hits and time stamps.
- The telescope can be used as a simple tracker
- ➢ KIT produced telescope cards carrying 4 sensors
 - with ~2.5 cm spacing



ATLASPix3

3.Beamtest @ DESY

D Experimental setup

- Device: two ATLAS Pix V3.1 telescopes + Quad Module
- \blacktriangleright Time of test: 4th 10th Apr, 2022
- ➤ Team members from KIT, Lancaster, Bristol, Milano, RAL, IHEP
- > Time Alignment: Reset the time stamps and hit count; Send out a check pulse
- \blacktriangleright Time drift correction: Time drift 1 ms/s 2 ms/s on average
- ➢ UDP, USB readout





Photo of the beamtest setup

Angle scan

Beam

Interleaving test

□ Test programmes

- Energy scan
 - Different beam energy: 6 GeV, 5.6 GeV, 5 GeV, 4 GeV, 2 GeV, 1.4 GeV, 1 GeV
 - To measure the patch scattering with different energy

Angle scan

- \succ Hits position ATLASPix3 3 Cluster P Sensor 3 hits distribution
- Cluster width
 - Cluster algorithm has no minimum seed value
 - Similar distribution on all 4 layers •
 - 1-pixel clusters dominate
- Cluster charge
 - Time-Over-Threshold calibration gives Landau disctribution of cluster charge with MPV around 5000e
 - Large plateau under study
- Track angle



HitmapATLASPix3_3 Sensor 3 hit map





• Expected longer clusters, with same time stamp,

- Different orientations of the telescopes: 0°, 11°, 20.5°, 28°, 40.5°, 45°, 86.5°
- To measure long track and clusters, also the charge sharing when hitting on the pixel edge and corner
- High Voltage scan
 - -48.6 V, -30 V, -20 V, -15 V, -10 V, -8 V, -6 V, -4 V, -2 V, 0 V
 - To measure the resolution difference against noise on chip due to the high voltage \bullet
- Interleaving test
 - Interleave 8 layers from 2 telescopes
 - To investigate track reconstruction between the 2 telescopes
- **D** Preliminary Results
 - \succ Hits position
 - Raw hit position from one run without masks or noise threshold shows noisy pixels at the edge
 - The beam is not centered, so the hitmap is sparse on the left and dense on the right
 - Hit position histograms correspond to hitmap



- Quad module
 - Pixel map: sample of 10⁷ hits chip 3 ~370 hits/s chip 4 \sim 250 hits/s
 - ToT histogram is similar with the Telescope's

same column and long rows or vice versa

- Timestamp difference result: maybe due to time walk
- Row number difference in a single event with same timestamp shows the longer cluster
- Tendency for longer clusters at high angle



◆ A lot of data is waiting to be analyzed

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